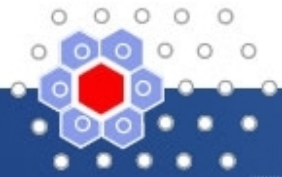


MONA
Merging Optics & Nanotechnologies

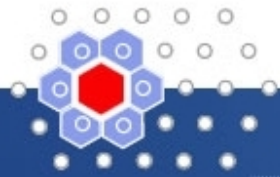
Equipment for Nanophotonics

Rainer Beccard
AIXTRON AG

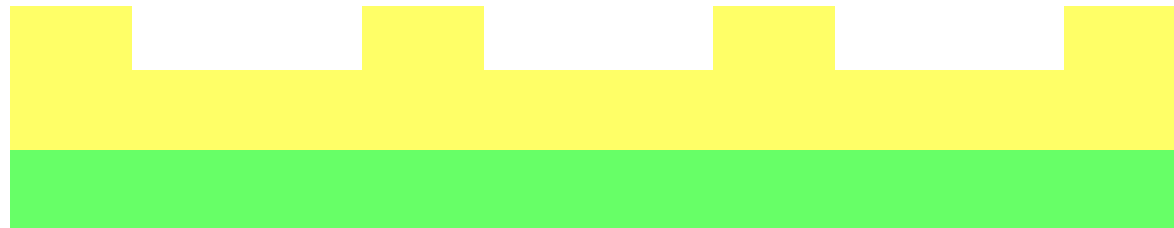
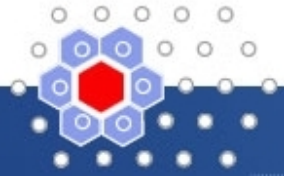
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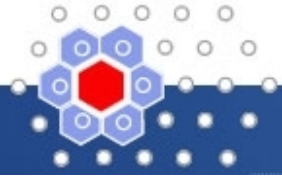


- ◆ Equipment categories to be considered
 - Equipment for bottom up approach
 - Equipment for top down approach
 - Metrology equipment

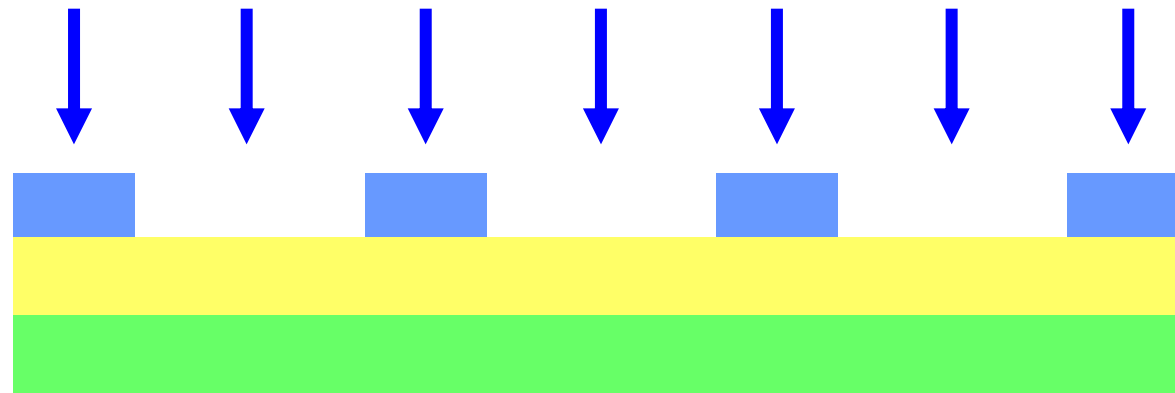
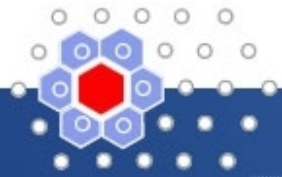


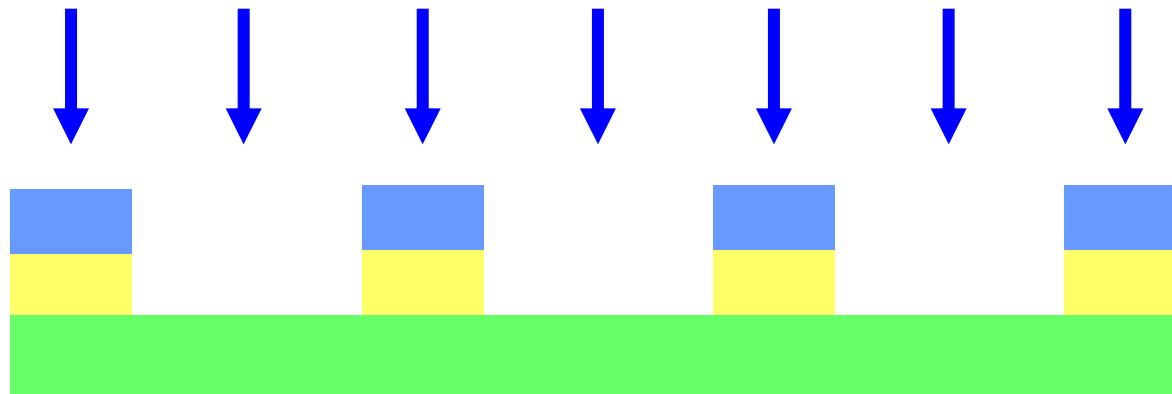
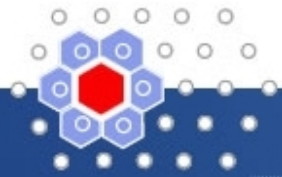
- Bottom up approach:
 - PVD/MBE (molecular beam epitaxy) → inorganic materials, III-Vs, II-VIs
 - [MO]CVD ([metal organic] chemical vapor deposition) → inorganic materials, III-Vs, II-VIs, Si, Oxides; self assembly
 - Printing (e. g. ink jet printing) → organic materials, polymers
 - OVPD (organic vapor phase deposition) → organic materials, small molecules

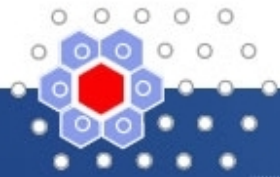




- Top down approach:
 - Optical lithography
 - E-beam / x-ray / ion beam lithography
 - Dry etching
 - Nano imprint / soft lithography

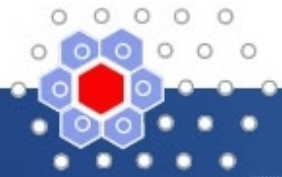






➤ Metrology

- SEM
- AFM
- TEM
- Reflectometry
- Ellipsometry
- In situ metrology for bottom up techniques



◆ Equipment for bottom up approach

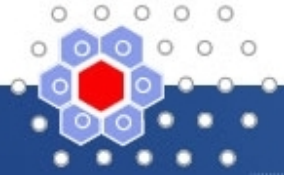
➤ MBE

- Current status: Multi 6 inch MBE available
- Standard equipment used for nano applications
- QD growth (III-V) established (lasers / amplifiers)
- Early stage of commercialization
- Future: more sophisticated nano devices → gas source or solid source MBE might be required



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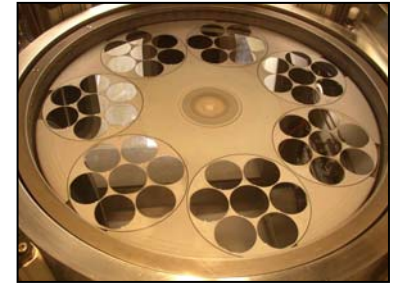
Source: Riber



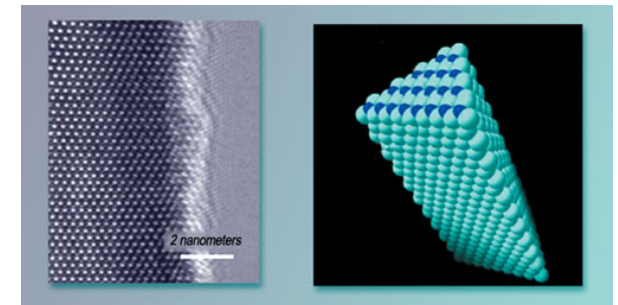
Equipment for bottom up approach

➤ MOCVD

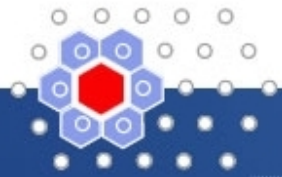
- Current status: Multi 8 inch MOCVD available
- Standard equipment used for nano applications
- Self-assembled growth of low dimensional structures established for GaAs, InP, GaN, ZnO and related materials
- Catalyst induced growth of nano structures
- Very precise control of thin layers in one dimension is possible
- Customized solutions for nano applications available
- Future: Improve reproducibility
- In situ metrology will become much more important (reflectometry, RAS,...)
- Transformation of promising R&D results into industry



Source: AIXTRON



Source: Berkeley Labs



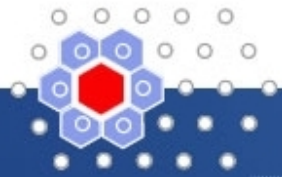
- ◆ Equipment for bottom up approach
 - other CVD: PECVD, ALD, ...
 - Current status: Standard and modified equipment is used for SiN, TiN, SiO, SiC, oxides (HfO, Al₂O₃), metals
 - No dedicated equipment available for nanophotonics
 - Nanophotonics do not play any important role today
 - Future: some potential?



Source: ASM



Source: Genus



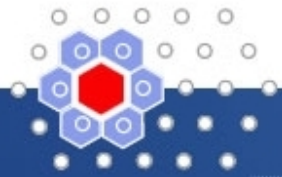
◆ Equipment for bottom up approach

➤ Printing

- Current status: Ink jet printing for full color displays (polymer OLEDs)
- Non-standard equipment used
- Screen printing: not working on nano scale, but used to deposit nano materials
- Future: dedicated equipment for nano applications
- Structuring / modification of deposited layers on nano scale



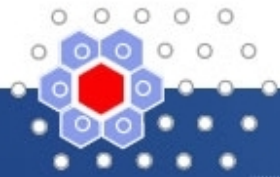
Source: Litrex



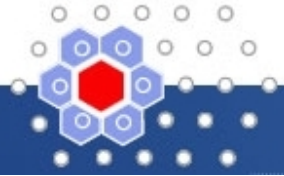
- ◆ Equipment for bottom up approach
 - Organic Vapor Phase Deposition (OVPD)
 - Current status: Technology exists for large area deposition of small molecule OLEDs on large area glasses
 - Nano resolution easily achieved in one dimension
 - Future: Lateral definition of nano structures



Source: AIXTRON



- ◆ Equipment for bottom up approach
 - Others:
 - Laser ablation / pulsed laser deposition (oxides)
 - CNT deposition (CVD, hot wall CVD)
 - Sputtering techniques
 - Spin coating
 - Sol-gel processes
 - Issues / future development:
 - Reproducibility
 - Scalability
 - No dedicated nano equipment available yet



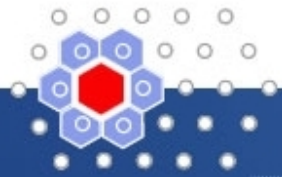
◆ Equipment for top down approach

➤ Optical lithography

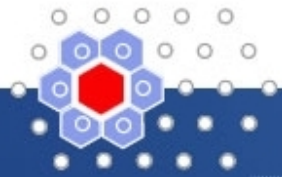
- Current status: well established technology down to 65 nm / 45 nm node (193 nm wavelength, immersion technology)
- Holographic lithography allows low cost production of periodic patterns
- Future: EUV required for definition of smaller structures (plasma or synchrotron UV sources); wavelength 13.4 nm



Source: ASML



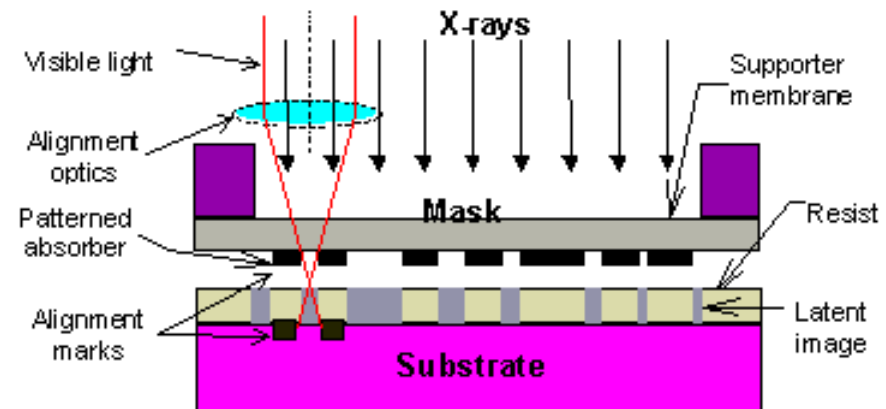
- ◆ Equipment for top down approach
 - E-beam lithography
 - Current status: allows definition of very small structures; not limited by wavelength but by various other effects
 - SEM type equipment; not suited for volume production
 - Future: E-beam projection lithography (higher throughput)



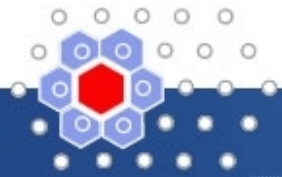
Equipment for top down approach

➤ X-ray lithography

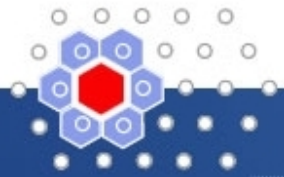
- Very short wavelength (0.01 – 1 nm)
- Tough requirements for masks
- X-ray generation by synchrotron required
- No industrial scale use so far



Source: Maxlab



- ◆ Equipment for top down approach
 - Ion beam lithography
 - Resolution down to 30 nm
 - Focused ion beam (scanning principle, no mask) or
 - Ion projection lithography (using masks)



◆ Equipment for top down approach

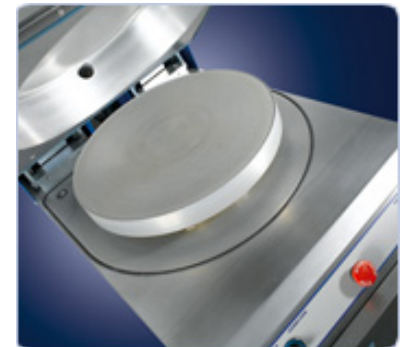
➤ Dry etching

- Current status: Reactive ion etching and ion beam etching well established
- Standard equipment currently used for nano applications
- Dry etching techniques used for nano applications in R&D scale
- Nano applications not limited by equipment
- Future: Reproducibility of dry etching in combination with masks and materials is critical

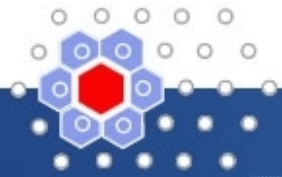


Source: STS

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Source: Oxford Instruments



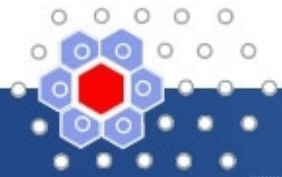
◆ Equipment for top down approach

➤ Nano imprint / soft lithography

- Current status: Technology is available for Si, III-Vs
- Part of ITRS roadmap
- Structure size down to 50 nm (R&D stage)
- Future: Improvements on accuracy, defects, reproducibility
- Throughput to be increased to meet industrial needs



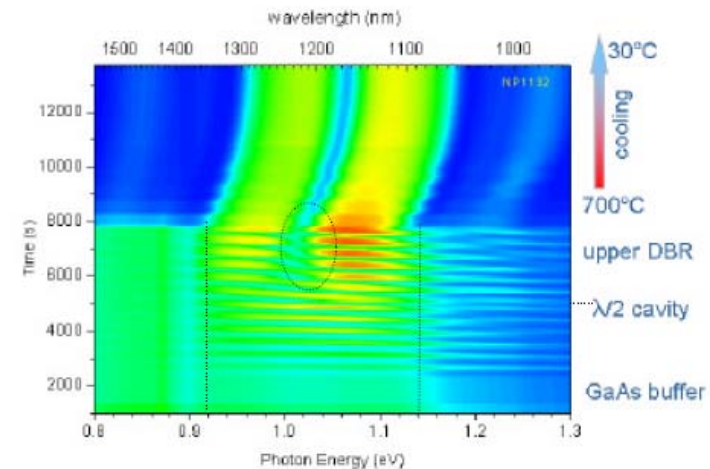
Source: Molecular Imprints



◆ Metrology equipment

➤ Current issues:

- Reliability
- Standardization
- Calibration
- In situ metrology: Transfer from R&D stage to industrial scale; choice of suited in situ methods



Source: Laytec